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Publication date:
2013

[Link back to DTU Orbit](#)

Citation (APA):
Jokubavicius, V., Sun, J., Linnarsson, M. K., Liljedahl, R., Kaiser, M., Wellmann, P., Ou, Y., Ou, H., Yakimova, R., & Syväjärvi, M. (2013). *Doping and stability of 3C-SiC: from thinfilm to bulk growth*. Abstract from E-MRS 2013 Spring Meeting, Strasbourg, France.

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Doping and stability of 3C-SiC: from thinfilm to bulk growth

V. Jokubavicius^a, J. Sun^b, M. K. Linnarsson^c, R. Liljedahl^d, M. Kaiser^e,
P. Wellmann^f, Y. Ou^g, H. Ou^h, R. Yakimova^j and M. Syväjärvi^k

Email: valjo@ifm.liu.se

^{a,b,d,j,k}Department of Physics, Chemistry and Biology, Linköping University, S581 83 Linköping, Sweden

^cSchool of Information and Communication Technology, KTH Royal Institute of Technology, SE-16440 Kista, Sweden

^{g, h}Department of Photonics Engineering, Technical University of Denmark, DK-2800 Lyngby, Denmark

^{e,f} Department of Material Science – Electrical Engineering Materials (WW6), University of Erlangen-Nuremberg, Martensstr. 7, 91058 Erlangen, Germany

Cubic silicon carbide (3C-SiC) could pave the way for development of advanced electronic and optoelectronic devices. It could be an excellent substrate for growth of nitride and epitaxial graphene layers. Boron doped 3C-SiC films could reach up to 60% efficiency and pave the way for a new solar cell technology. Nitrogen and boron doped 3C-SiC layers can depict a new infrared LED.

Hexagonal SiC is an excellent substrate for heteroepitaxial growth of 3C-SiC due to excellent compatibility in lattice constant and thermal expansion coefficient. However, the growth of 3C-SiC on such substrates is still being followed by a number of obstacles like polytype stabilization and high density of double positioning boundaries in the grown material. The polytype stability during epitaxial growth of doped 3C-SiC has not been explored. Consequently, the polytype stability during bulk growth of doped 3C-SiC is not known.

In this study we explore the growth of low and medium doped bulk-like 3C-SiC layers on off-oriented 6H-SiC substrates using a sublimation epitaxy technique. We compare SIMS, XRD and PL data obtained from 3C-SiC material grown using polycrystalline SiC sources prepared by CVD with a low ($\sim 10^{16}\text{cm}^{-3}$) boron concentration and by PVT with a medium ($\sim 10^{18}\text{cm}^{-3}$) nitrogen and boron concentrations. The effects of impurities on polytype stability and crystal quality of low and medium doped bulk-like 3C-SiC layers with thickness up to 0.5 mm are analysed. Moreover, the remaining challenges in growth of 3C-SiC for optoelectronic applications are discussed.